HALOGEN

FREE





Low Voltage, Dual DPDT in miniQFN16

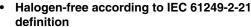
DESCRIPTION

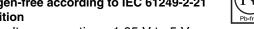
The DG2599 is a C_{MOS} Dual DPDT (Dual Double Pole Double Throw) analog switch that operates over a wide voltage range of 1.65 V to 5 V. It is optimized for portable applications switching audio, SIM card signals, and other low power signals.

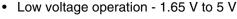
The DG2599 features low ON resistance of 2.8 Ω at 3 V power supply, fast switching speed, and low power consumption even when control logic signals are below V+ power supply voltage. The well matched dual DPDT switches conduct signals equally in both directions. The DG2599 is designed to guarantee break before make switching.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. DG2599 are offered in a miniQFN package. The miniQFN package has a nickel palladium- gold device termination and is represented by the lead (Pb)-free "-E4" suffix. The nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL ratings.

FEATURES







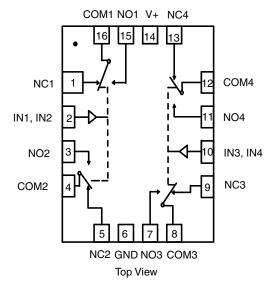
- Low on-resistance 2.8 Ω at V+ = 3 V
- Power off protection on COM1 and COM2 pins Latch up current great than 300 mA per JESD78



APPLICATIONS

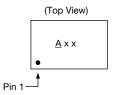
- · Cellular phones
- · PMPs and PDAs
- Modems and peripherals
- Computers and ebooks
- Tablet devices
- Displays and gaming
- STB

ORDERING INFORMATION					
Part Number	Package				
DG2599DN-T1-GE4	miniQFN16 1.8 mm x 2.6 mm				



TRUTH TABLE (DG2599)				
Logic	Logic NC1, 2, 3 and 4 NO			
0	ON	OFF		
1	OFF	ON		

Device Marking: A xx xx = Date/Lot Traceability Code



Note: Pin 1 has long lead



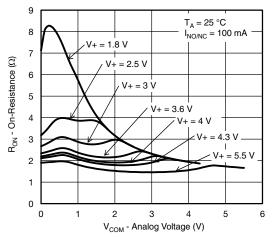
ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter	Symbol	Limit	Unit		
Reference to GND	V+		- 0.3 to 5	V	
Reference to GND	IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)		
Current (any terminal except NO, NC or		30			
Continuous Current (NO, NC, or COM)		± 300	mA		
Peak Current (pulsed at 1 ms, 10 % duty		± 500			
Storage Temperature (D Suffix)		- 65 to 150			
Package Solder Reflow Conditions ^d	miniQFN16		250	°C	
Power Dissipation (Packages) ^b	miniQFN16 ^c		525	mW	

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6.6 mW/°C above 70 °C.
- d. Manual soldering with iron is not recommended for leadless components. The miniQFN-16 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

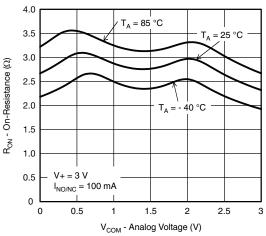
Parameter	Test Conditions	Temp.	Min.	Тур.	Max.	Unit	
Power Supply and Signal							
V+ Supply Voltage		Full	1.65		5	V	
V+ Supply Current	V _{IN} = 0 or V+	Full		0.001	2	μΑ	
Analog Signal Range		Full	0		V+	V	
Switch On-Resistance and Leakag	е						
Drain-Source On-Resistance	V+ = 3 V, I _{NO/NC} = 100 mA, V _{COM} = 0.9 V, 2.3 V			2.8	3.3	Ω	
Brain Gource On Tresistance					3.6		
On-Resistance Flatness	$V+ = 3 \text{ V}, I_{NO/NC} = 100 \text{ mA}, V_{COM} = 0 \text{ to } V+$	Room		0.24	1.1	3.2	
On Hosistanoo Hatricos	VI = 0 V, INO/NC = 100 III/I, VCOM = 0 to VI	Full			1.3		
Switch Off Leakage Current	$V_{+} = 4.3 \text{ V}, V_{NO/NC} = 0.3 \text{ V/4 V}, V_{COM} = 4 \text{ V} / 0.3 \text{ V}$	Room	- 10	0.1	10		
Ownor on Leanage Carrent	V 1 = 4.5 V, V _{NO/NC} = 0.5 V/4 V, V _{COM} = 4 V / 0.5 V	Full	- 100		100	nA	
Channel On-Leakage Current	$V+ = 4.3 \text{ V}, V_{NO/NC} \text{ and } V_{COM} = 0.3 \text{ V} / 4 \text{ V}$	Room	- 10	0.1	10	- IIA	
Charmer on Leanage Carrent	V1 = 4.8 V, V _{NO/NC} and V _{COM} = 8.8 V / 4 V	Full	- 100		100		
Digital Control							
Input, High Voltage	V+ = 4.3 V	Full	1.6			V	
mpat, riigir voltage	V+ = 3 V		1.3				
Input, Low Voltage	V+ = 4.3 V	Full			0.6		
mput, 2011 Voltago	V+ = 3 V				0.5		
Input, Bias Current	$V_{IN} = V+$	Full	- 1	0.01	1	μΑ	
Dynamic Characteristics							
Turn On-Time	V_{COM} or $V_{NO/NC} = 3$ V, $R_L = 50 \Omega$, $C_L = 35$ pF	Room			90		
	COM S. THOING S.	Full			115		
Turn Off-Time	V_{COM} or $V_{NO/NC} = 3$ V, $R_L = 50 \Omega$, $C_L = 35$ pF	Room			70	ns	
	COM S. THOING S.	Full			85	-	
Break Before Make Time	V_{COM} or $V_{NO/NC} = 3$ V, $R_L = 50 \Omega$, $C_L = 35$ pF	Room Full	2				
Broak Boloro Make Time			2				
Charge Injection	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega$	Room		± 10		рC	
Off Isolation	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$			- 66			
Crosstalk	$R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 1 \ MHz$ Non-adjacent channels			- 110		dB	
3dB Bandwith	$C_L = 5 \text{ pF}, R_L = 50 \Omega$			186		MHz	
Source Off Capacitance	V _{IN} = 0 or V+, f = 1 MHz			9			
Channel On Capacitance	V _{IN} = 0 or V+, f = 1 MHz			26		pF	



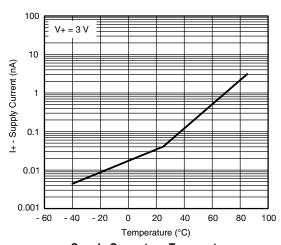
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



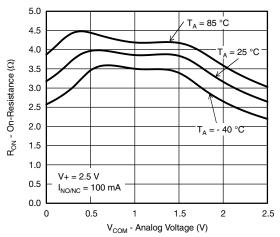
 $\rm R_{ON}$ vs. $\rm V_{COM}$ and Single Supply Voltage



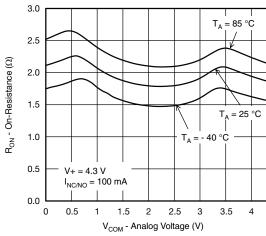
R_{ON} vs. Analog Voltage and Temperature



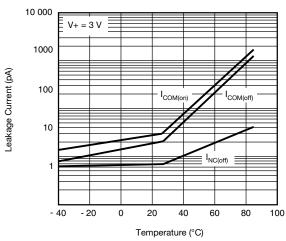
Supply Current vs. Temperature



R_{ON} vs. Analog Voltage and Temperature



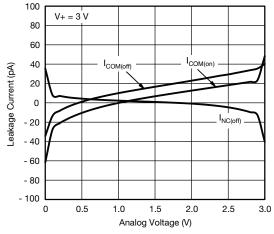
R_{ON} vs. Analog Voltage and Temperature



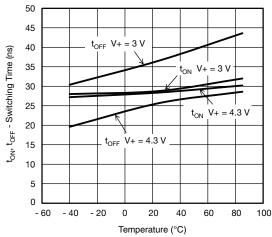
Leakage Current vs. Temperature

VISHAY

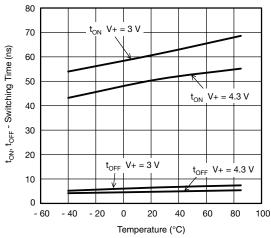
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



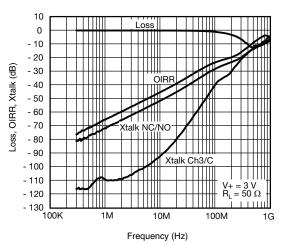
Leakage vs. Analog Voltage



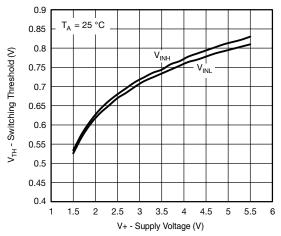
(NO) Switching Time vs. Temperature



(NC) Switching Time vs. Temperature

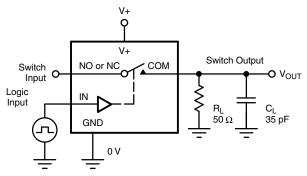


Insertion Loss, Off Isolation and Crosstalk



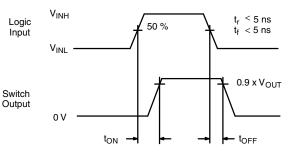
Switching Threshold vs. Supply Voltage

TEST CIRCUITS



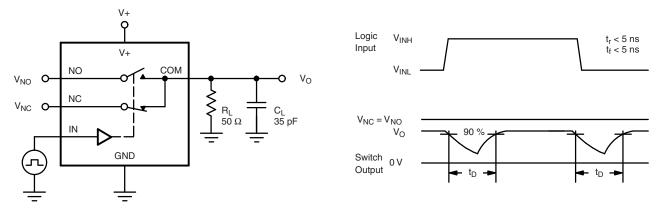
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{OM}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time



C_L (includes fixture and stray capacitance)

Figure 2. Break-Before-Make Interval

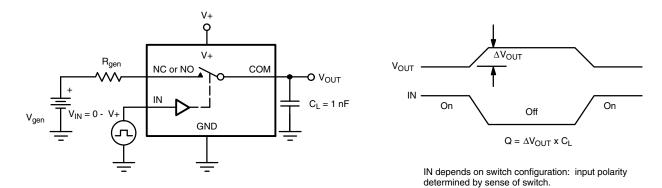


Figure 3. Charge Injection

TEST CIRCUITS

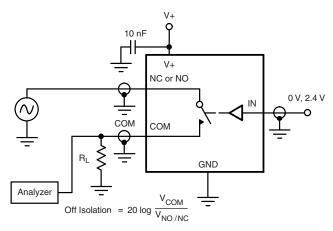


Figure 4. Off-Isolation

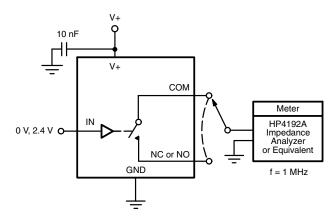
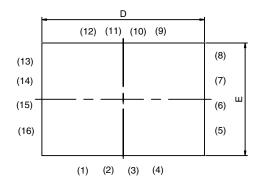


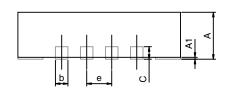
Figure 5. Channel Off/On Capacitance

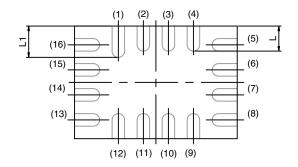
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67667.



MINI QFN-16L







BACK SIDE VIEW

DIM	MILLIMETERS			INCHES			
	MIN.	NAM	MAX.	MIN.	NAM	MAX.	
Α	0.70	0.75	0.80	0.0275	0.0295	0.0315	
A1	0	-	0.05	0	-	0.002	
b	0.15	0.20	0.25	0.0059	0.0078	0.0098	
С	0.15	0.20	0.25	0.0059	0.0078	0.0098	
D	2.60 BSC			0.1023 BSC			
Е	1.80 BSC			0.0708 BSC			
е	0.40 BSC			0.40 BSC 0.0157 BSC			;
L	0.35	0.40	0.45	0.0137	0.0157	0.0177	
L1	0.45	0.50	0.55	0.0177	0.0196	0.0216	

ECN T-06380-Rev. A, 14-Aug-06 DWG: 5954





Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 11-Mar-11